

SANYO Semiconductors DATA SHEET

2SD1230-

NPN Epitaxial Planar Silicon Darlington Transistor **Driver Applications**

Applications

• Motor drivers, printer hammer drivers, relay drivers, voltage reguraltor control.

Features

- High DC current gain.
- · High current capacity and wide ASO.
- Low saturation voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		110	V
Collector-to-Emitter Voltage	VCEO		100	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		8	A
Collector Current (Pulse)	ICP		12	A
Collector Dissipation	De		2.5	W
	PC	Tc=25°C	60	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	VCB=80V, IE=0A			0.1	mA
Emitter Cutoff Current	IEBO	VEB=5V, IC=0A			3	mA
DC Current Gain	hFE	V _{CE} =3V, I _C =4A	1500	4000		
Gain-Bandwidth Product	ŕΤ	VCE=5V, IC=4A		20		MHz

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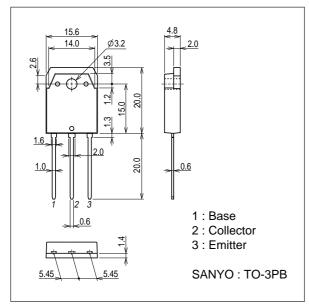
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=4A, IB=8mA		0.9	1.5	V
Base-to-Emitterr Saturation Voltage	V _{BE} (sat)	IC=4A, IB=8mA			2.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=5mA, IE=0A	110			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=50mA, RBE=∞	100			V
Turn-ON Time	ton	See specified Test Circuit		0.6		μs
Storage Time	tstg	See specified Test Circuit		4.8		μs
Fall Time	tf	See specified Test Circuit		1.6		μs

Package Dimensions

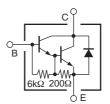
unit : mm (typ) 7503-003

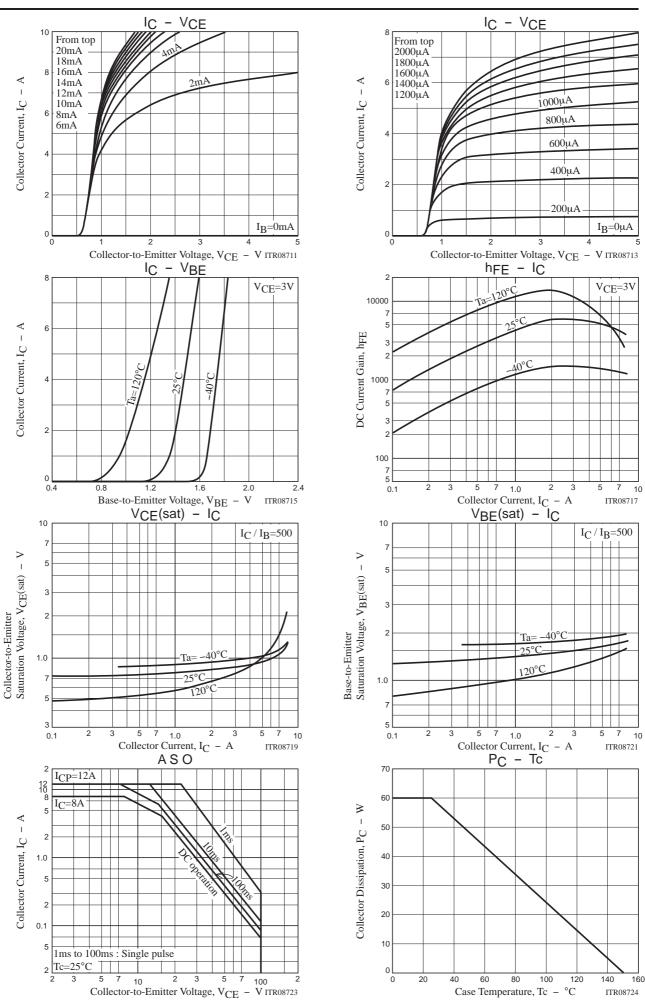


Switching Time Test Circuit

PW=50µs, Duty Cycle≤1% OUTPUT $500I_{B1} = -500I_{B2} = I_C = 4A$ TUT RB W ≷ RL | 12.5 50Ω≷ VR ₿+ ∄. 7777 470μF 100μF $\frac{1}{2}$ V_{CC}=50V o V_{BE}= -5V

Electrical Connection





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